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FIG. 1

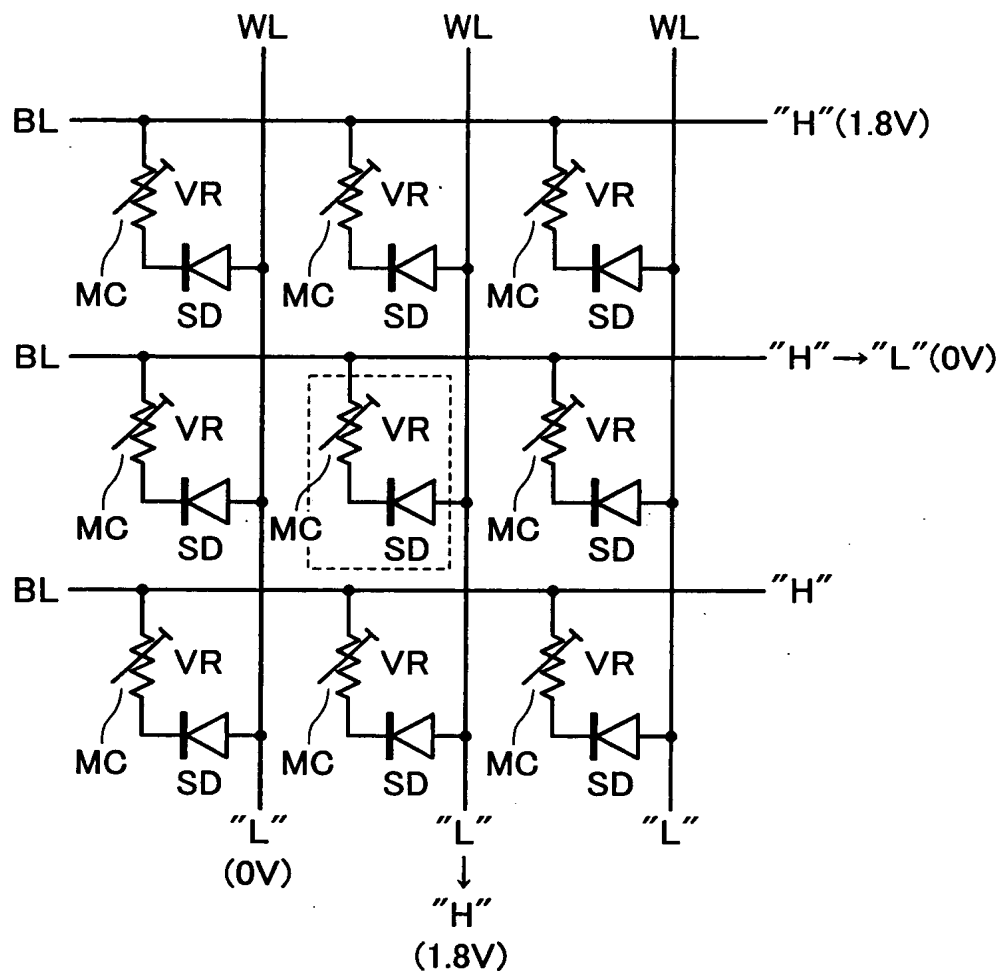
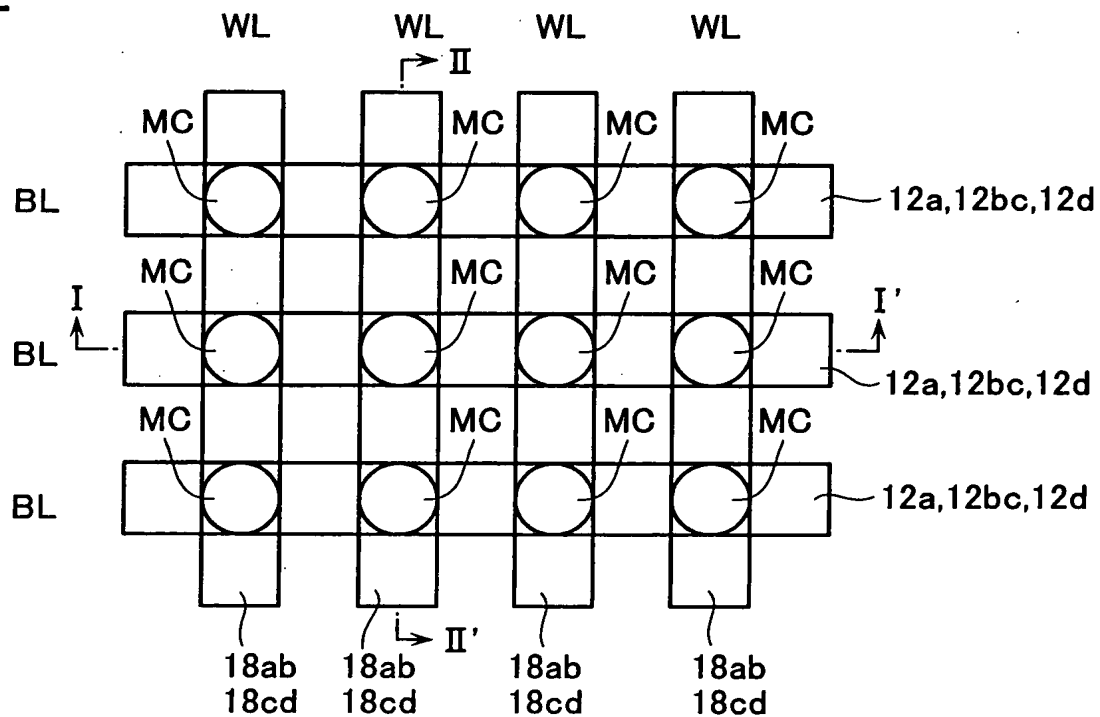
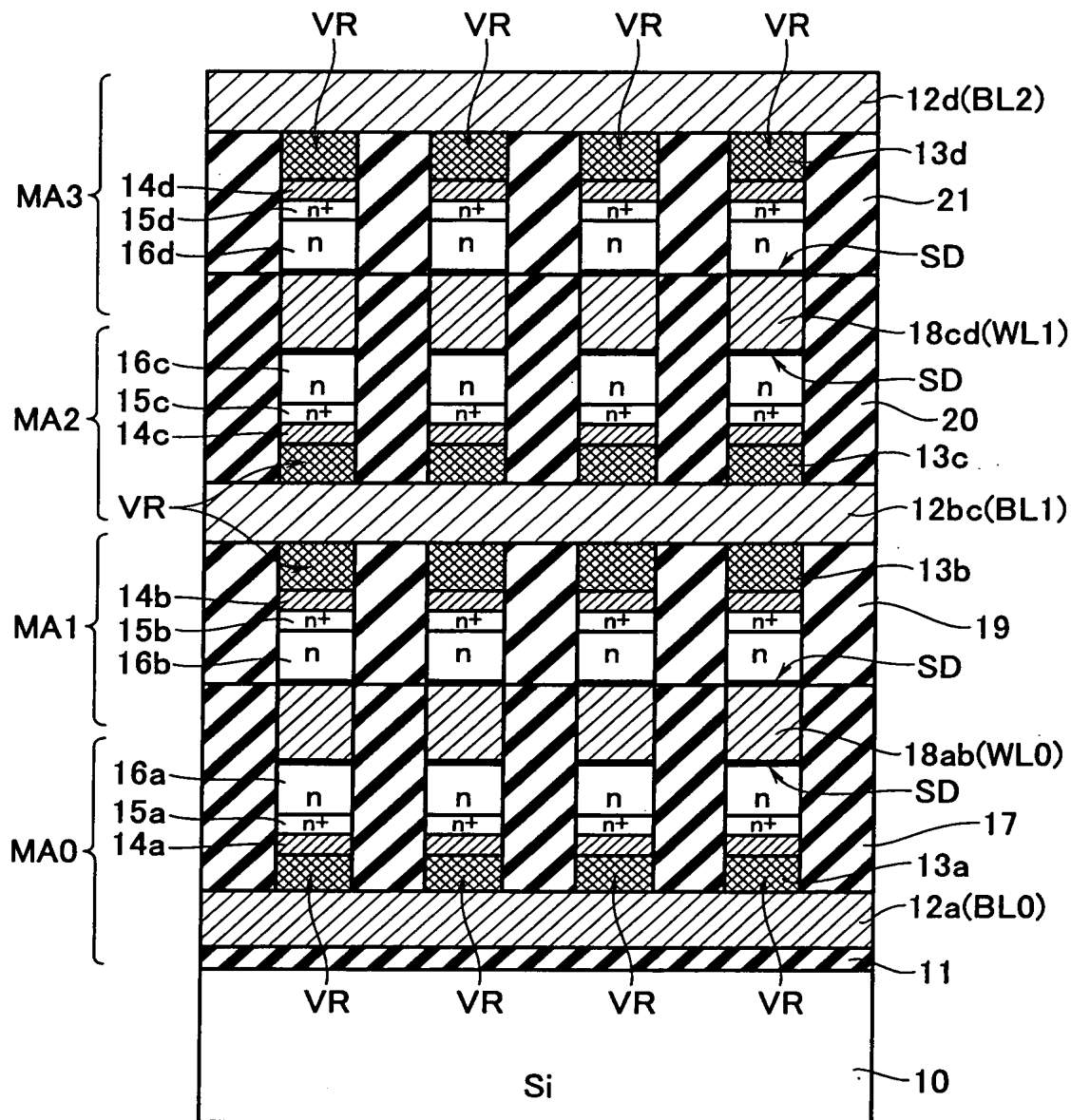


FIG. 2



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FIG. 3



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FIG. 4

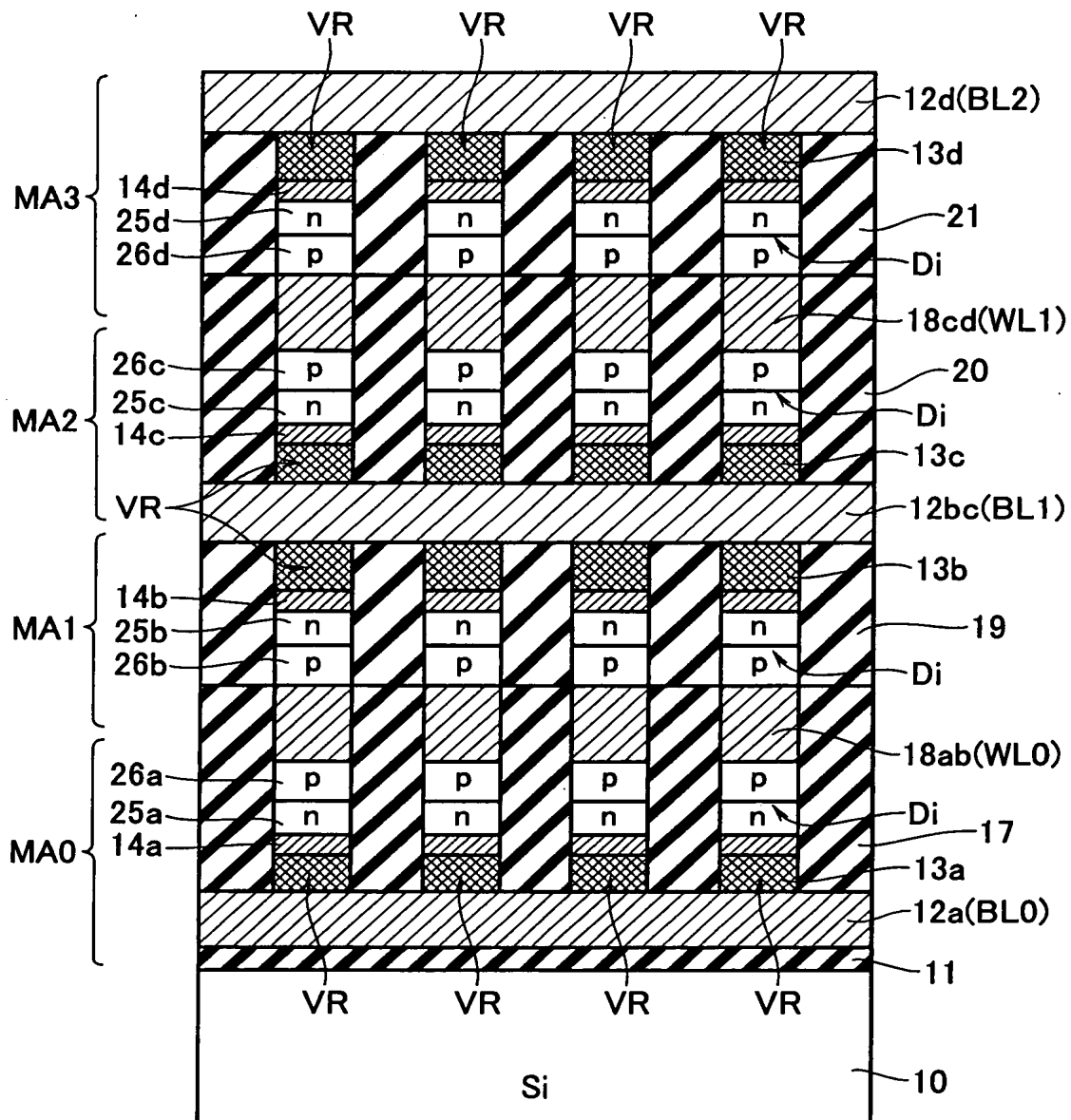
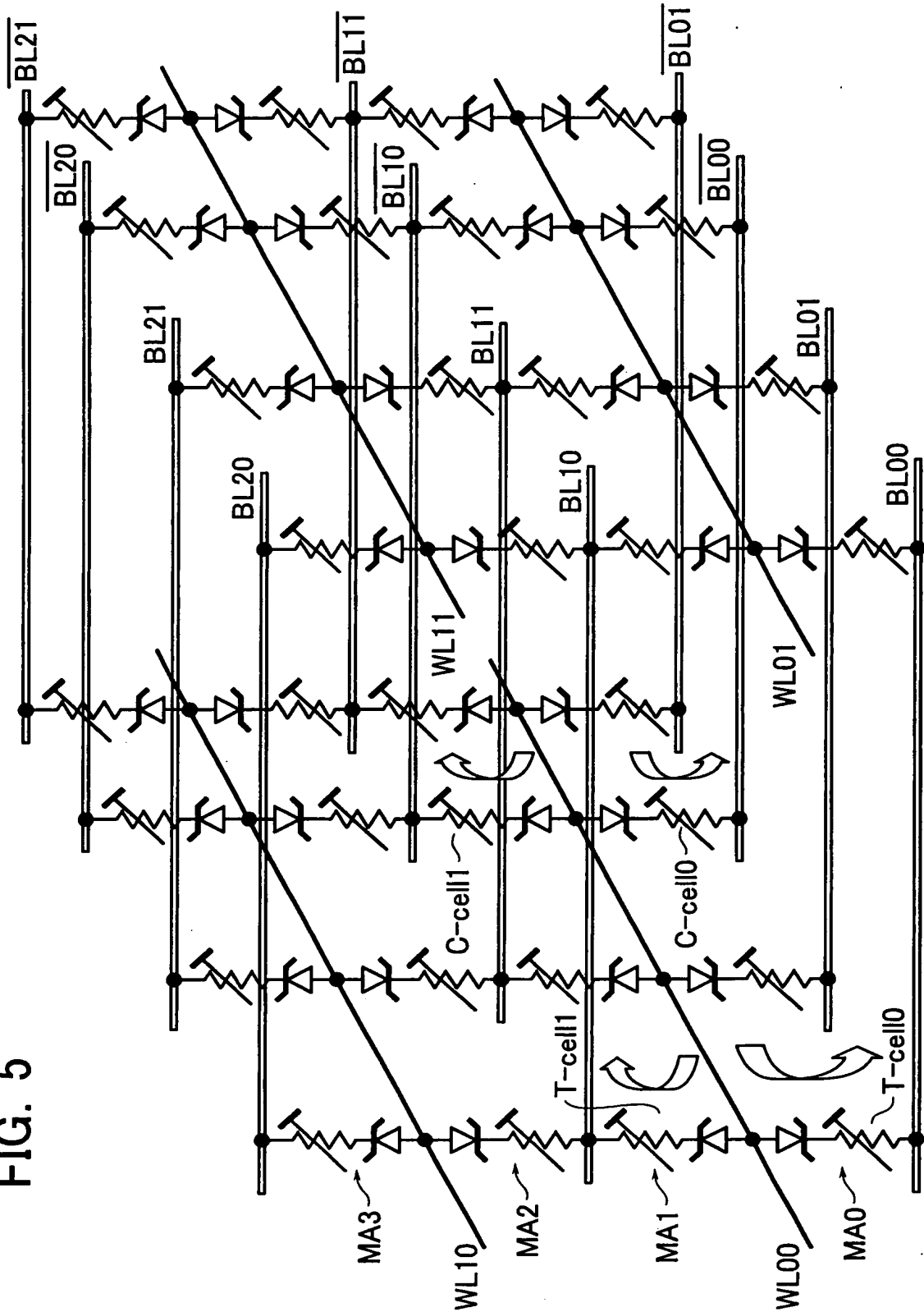


FIG. 5



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FIG. 6

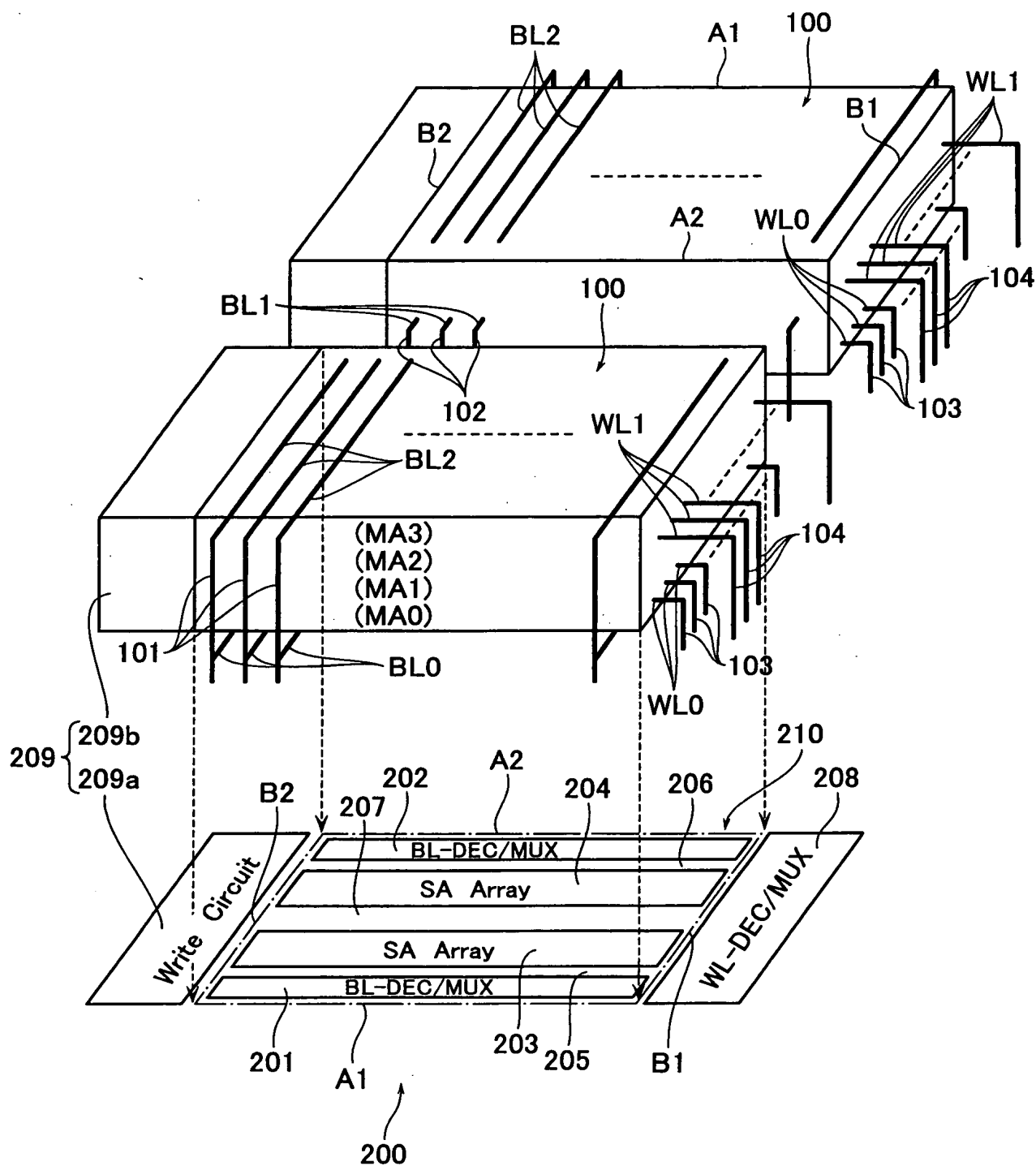


FIG. 11

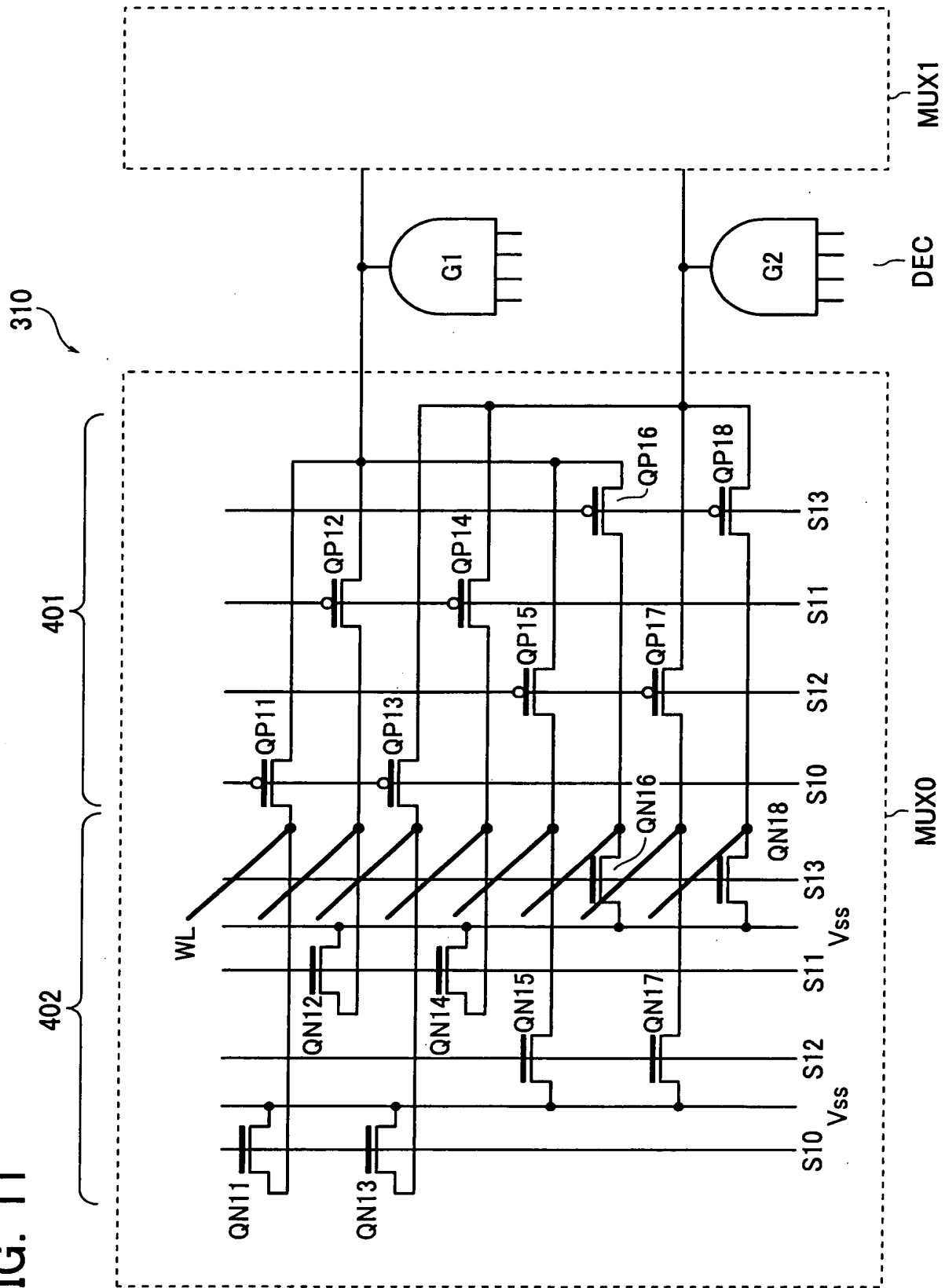
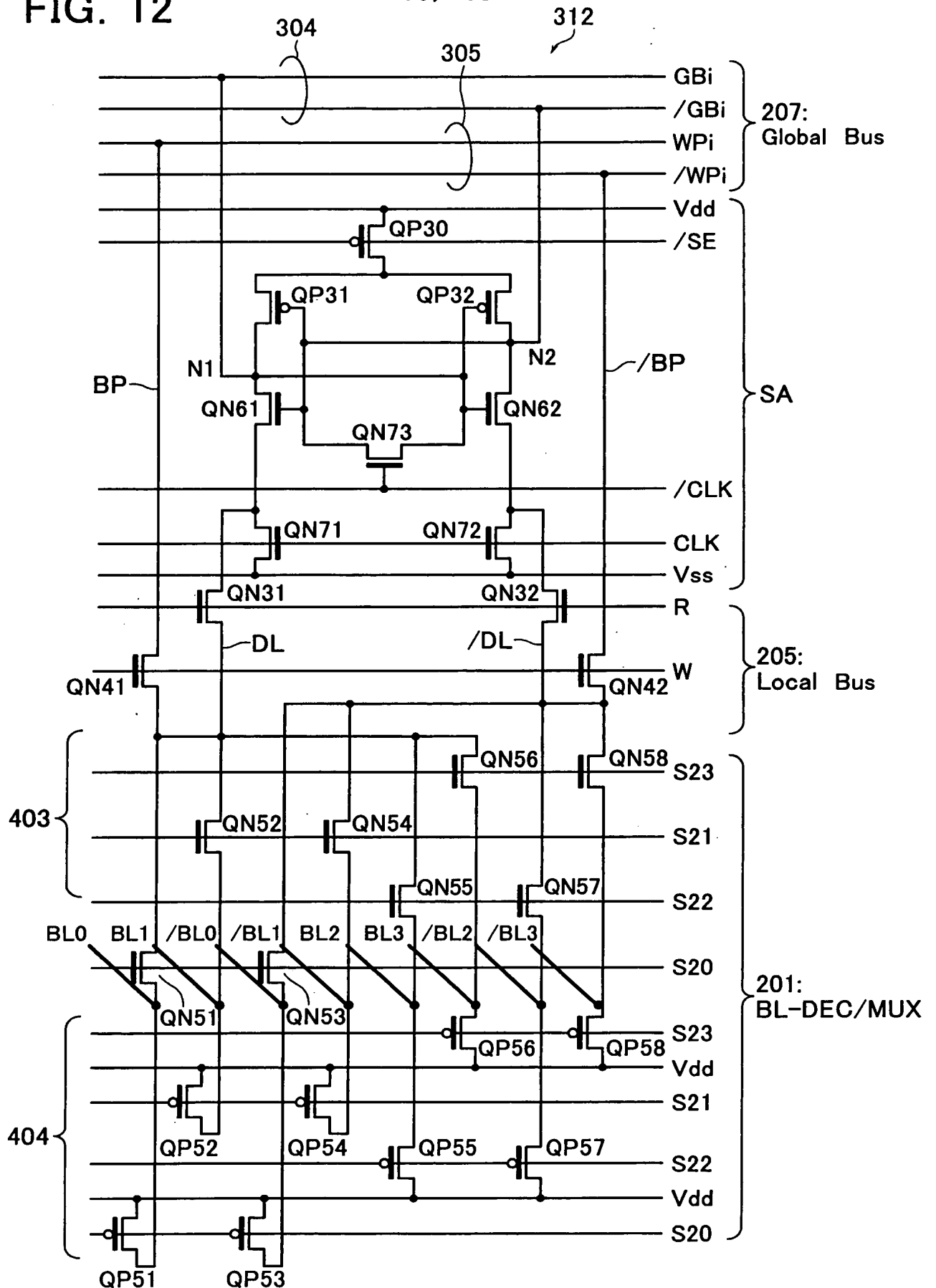


FIG. 12

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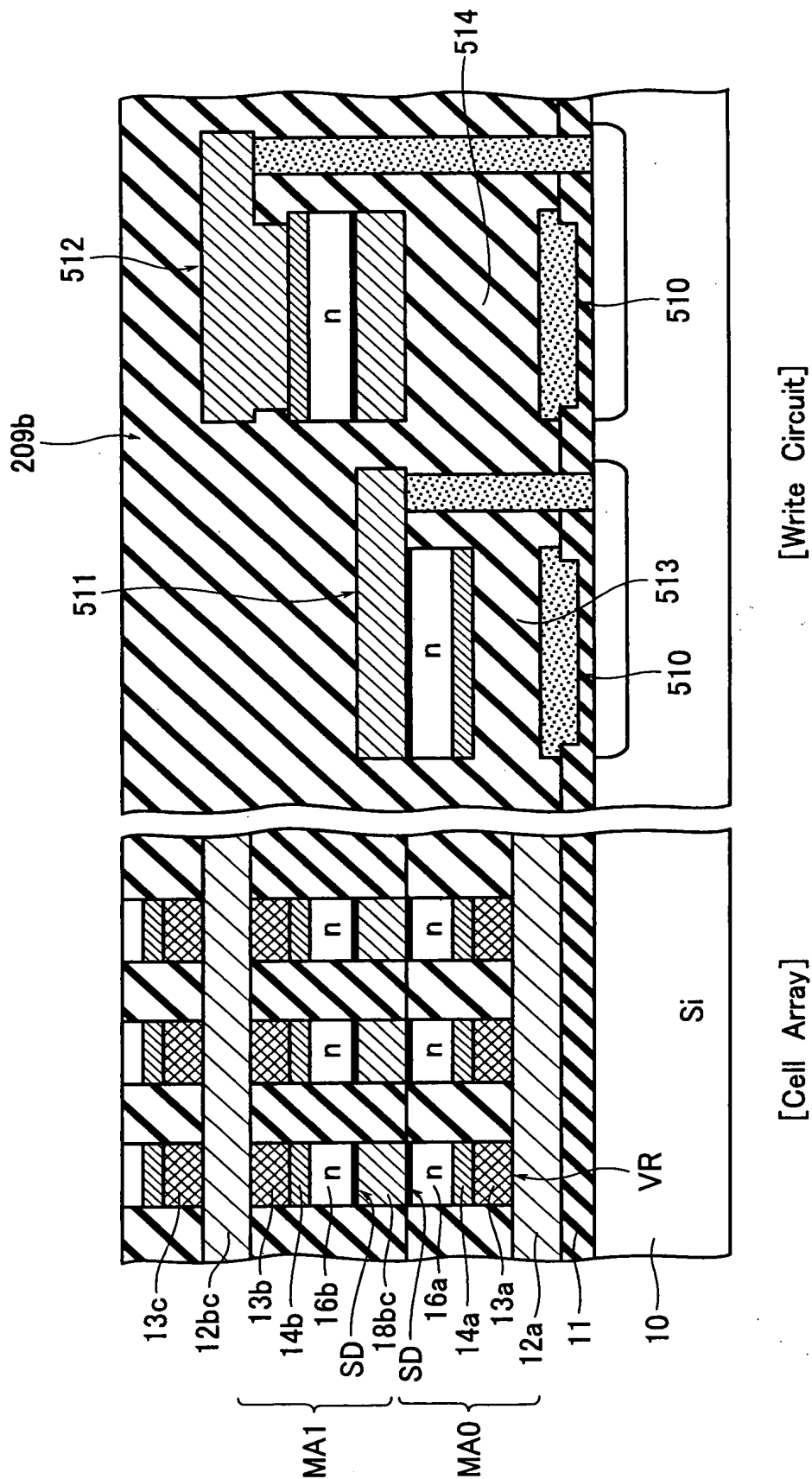


[illegible]

Figure 1 is a cross-sectional view of a semiconductor device 100. The device includes a substrate 10, a base layer 11, and a patterned layer 17. The patterned layer 17 is composed of a grid of rectangular features. The features are labeled 104b, 103b, MC, WL0, 104a, 103a, and BL0. The features 104b and 103b are located in the upper portion of the patterned layer 17, while the features 104a and 103a are located in the lower portion. The features MC and WL0 are located in the middle portion of the patterned layer 17. The features BL0 are located in the lower portion of the patterned layer 17, adjacent to the base layer 11. The features 104a and 103a are located in the lower portion of the patterned layer 17, adjacent to the base layer 11. The features 104b and 103b are located in the upper portion of the patterned layer 17. The features MC and WL0 are located in the middle portion of the patterned layer 17. The features BL0 are located in the lower portion of the patterned layer 17, adjacent to the base layer 11.

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FIG. 18



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FIG. 21

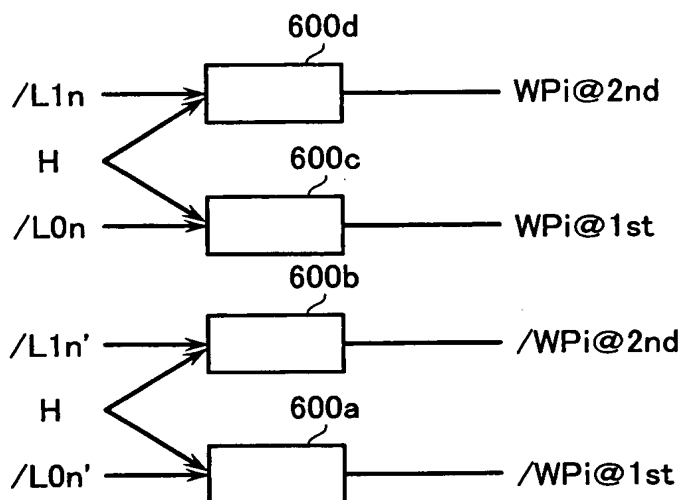


FIG. 22

